03/13/2008

Reply to final Office Action mailed January 29, 2008

Listing of the Claims

The following Listing of the Claims will replace all prior versions, and listings, of claims in the Application.

1. (Currently Amended) A method for planarizing a semiconductor wafer having an insulating layer on a surface thereof, the insulating layer comprising a field region and a plurality of features each including a feature cavity, the method comprising the steps of:

forming a barrier layer overlying at least the field region;

electrodepositing a layer comprising copper having a substantially planar upper surface overlying the barrier layer and filling at least a majority of each feature cavity; and

chemical mechanical planarizing polishing the layer comprising copper and the barrier layer on a single soft polishing pad to remove the layer comprising copper and the barrier layer from the field region and produce a substantially planar surface.

- 2. (Cancelled).
- 3. (Previously Presented) The method of claim 1 wherein the step of polishing comprises the step of chemical mechanical planarizing on a polishing pad having a hardness less than about 0.4 on the Shore D hardness scale.
- 4. (Previously Presented) The method of claim 1 wherein the step of chemical mechanical planarizing comprises the step of chemical mechanical planarizing in the presence of a polishing slurry having a copper:barrier layer selectivity of substantially 1:1.
- 5. (Previously Presented) The method of claim 1 wherein the step of chemical mechanical planarizing comprises the steps of: